

BTA201W series E

1 A Three-quadrant triacs high commutation

Rev. 03 — 13 March 2008

Product data sheet

1. Product profile

1.1 General description

Passivated guaranteed commutation triacs in a surface-mounted plastic package, intended for interfacing with low-power drivers, including microcontrollers.

1.2 Features

- Suitable for interfacing with low-power drivers, including microcontrollers
- SOT223 surface mounted

1.3 Applications

- Motor control
- Solenoid drivers

1.4 Quick reference data

- $I_{TSM} \leq 12.5$ A
- $I_{T(RMS)} \leq 1$ A
- $V_{DRM} \leq 600$ V (BTA201W-600E)
- $V_{DRM} \leq 800$ V (BTA201W-800E)
- $I_{GT} \leq 10$ mA (BTA201W-600E)
- $I_{GT} \leq 10$ mA (BTA201W-800E)
- $I_{GT} \geq 1$ mA (BTA201W-600E)
- $I_{GT} \geq 1$ mA (BTA201W-800E)

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	main terminal 1 (T1)	<p>SOT223</p>	<p>sym051</p>
2	main terminal 2 (T2)		
3	gate (G)		
4	main terminal 2 (T2)		

3. Ordering information

Table 2. Ordering information

Type number	Package		Version
	Name	Description	
BTA201W-600E	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223
BTA201W-800E			

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage	BTA201W-600E	[1] -	600	V
		BTA201W-800E	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{sp} ≤ 106 °C; see Figure 4 and 5	-	1	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; T _j = 25 °C prior to surge; see Figure 2 and 3			
		t = 20 ms	-	12.5	A
		t = 16.7 ms	-	13.7	A
I ² t	I ² t for fusing	t _p = 10 ms	-	0.78	A ² s
di _T /dt	rate of rise of on-state current	I _{TM} = 1.5 A; I _G = 0.2 A; di _G /dt = 0.2 A/μs	-	100	A/μs
I _{GM}	peak gate current		-	2	A
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	+150	°C
T _j	junction temperature		-	125	°C

- [1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/μs.

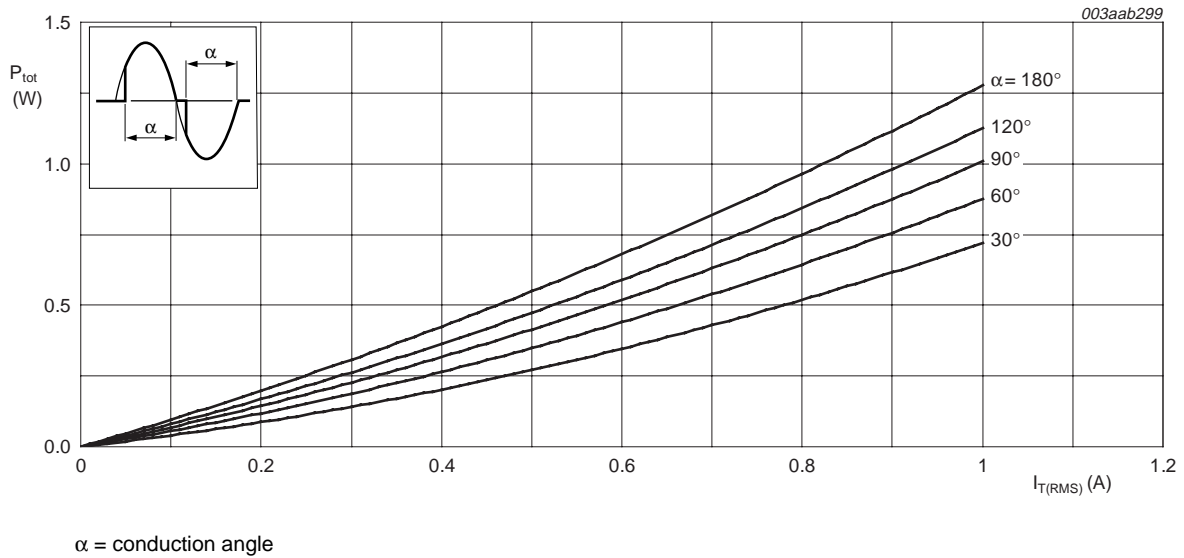


Fig 1. Total power dissipation as a function of RMS on-state current; maximum values

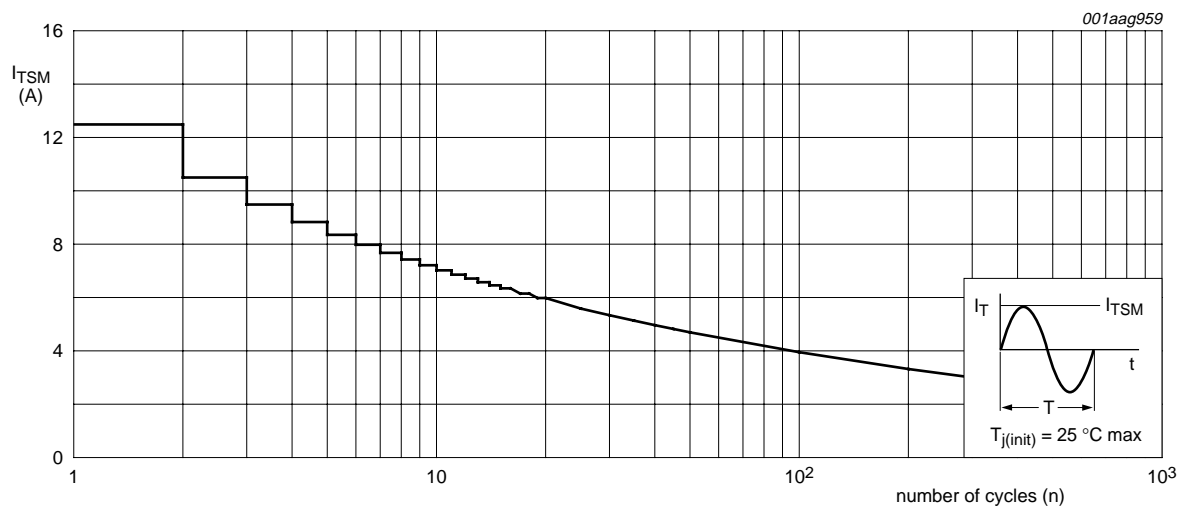
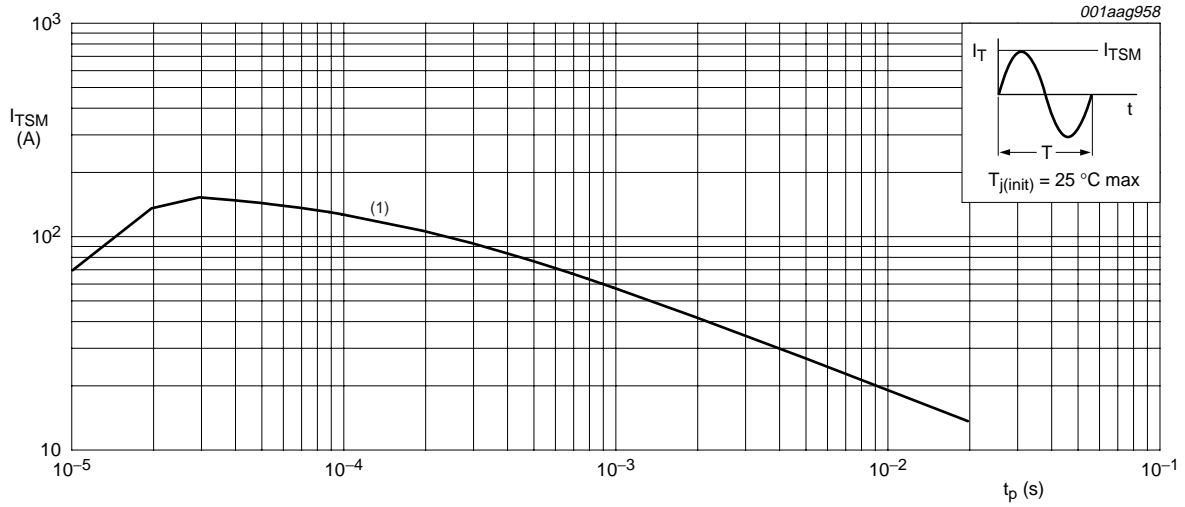
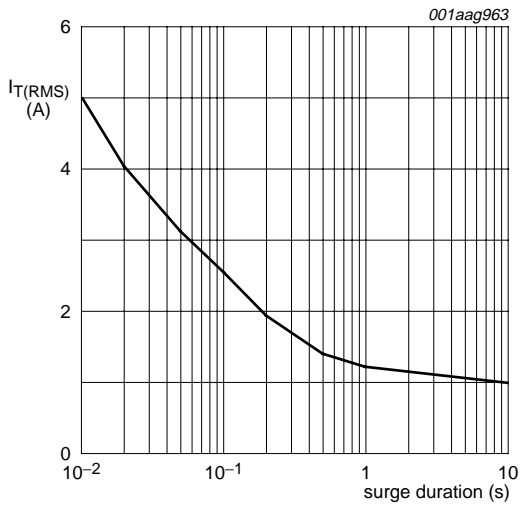


Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20\text{ ms}$
 (1) di_T/dt limit

Fig 3. Non-repetitive peak on-state current as a function of pulse width; maximum values



$f = 50\text{ Hz}; T_{sp} = 106\text{ °C}$

Fig 4. RMS on-state current as a function of surge duration; maximum values

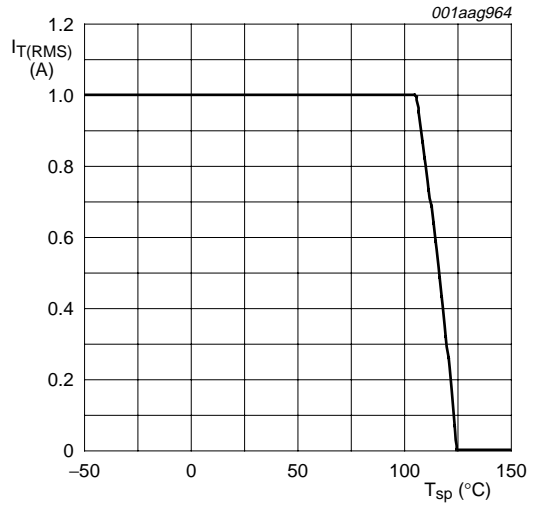


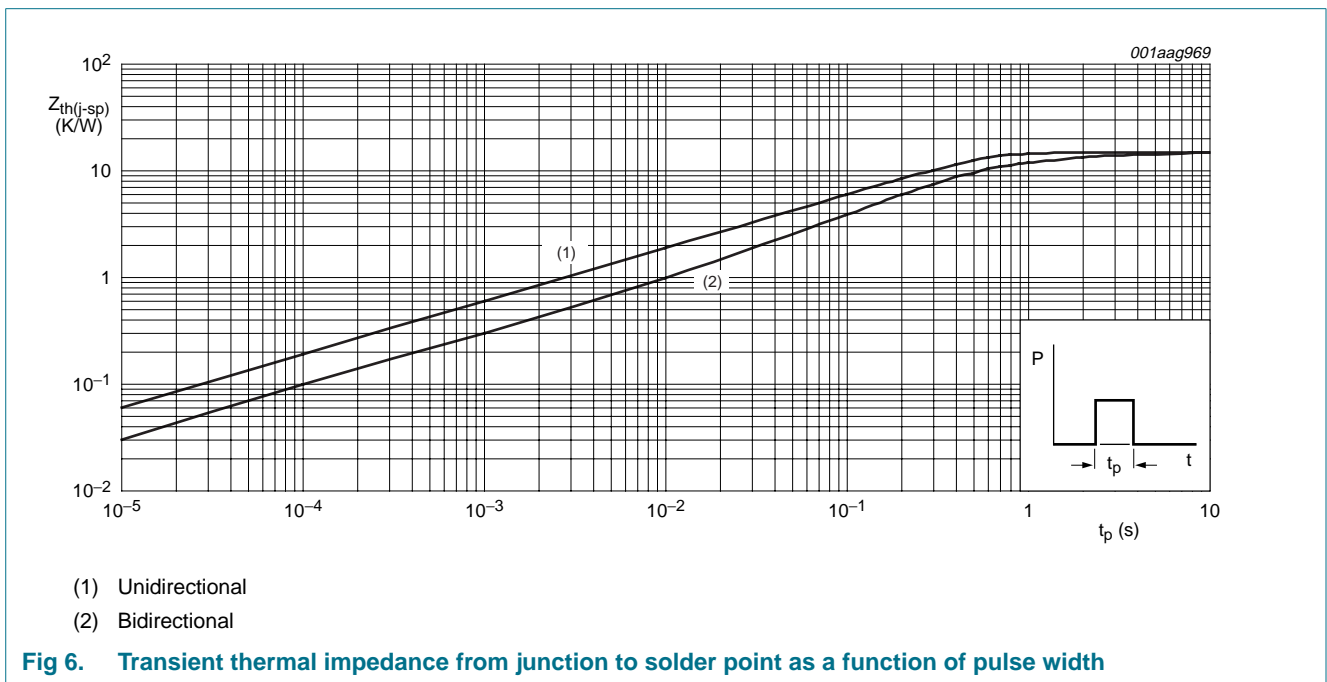
Fig 5. RMS on-state current as a function of solder point temperature; maximum values

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	see Figure 6	-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; see Figure 14	[1] -	156	-	K/W
		for pad area; see Figure 15	[1] -	70	-	K/W

[1] Mounted on a printed-circuit board.



6. Static characteristics

Table 5. Static characteristics

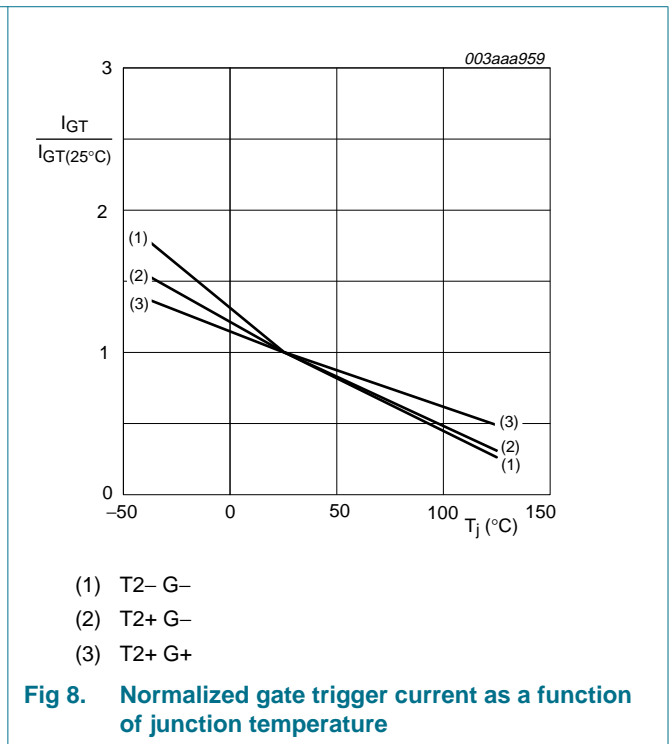
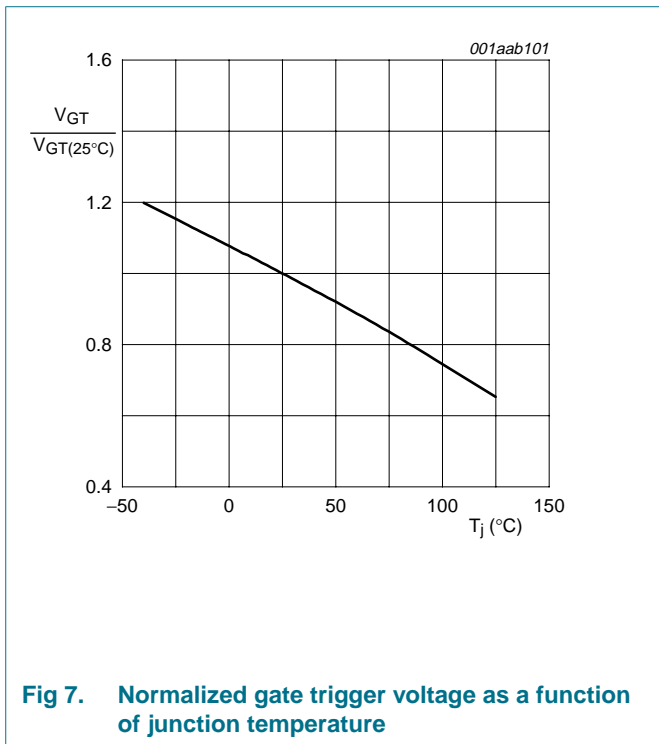
$T_j = 25\text{ °C}$ unless otherwise specified.

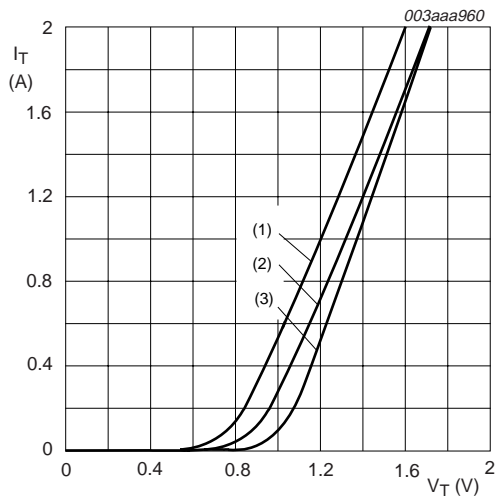
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
BTA201W-600E and BTA201W-800E						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; see Figure 8				
		T2+ G+	1	-	10	mA
		T2+ G-	1	-	10	mA
		T2- G-	1	-	10	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; see Figure 10				
		T2+ G+	-	-	12	mA
		T2+ G-	-	-	20	mA
		T2- G-	-	-	12	mA
I_H	holding current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; see Figure 11	-	-	12	mA
V_T	on-state voltage	$I_T = 1.4\text{ A}$; see Figure 9	-	1.2	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; see Figure 7	-	0.7	1.5	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ °C}$	0.2	0.3	-	V
I_D	off-state current	$V_D = V_{DRM(max)}$; $T_j = 125\text{ °C}$	-	0.1	0.5	mA

7. Dynamic characteristics

Table 6. Dynamic characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
BTA201W-600E and BTA201W-800E						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 0.67V_{DRM(max)}$; $T_j = 125\text{ }^\circ\text{C}$; exponential waveform; gate open circuit	600	-	-	V/ μs
di_{com}/dt	rate of change of commutating current	$V_{DM} = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 4\text{ A}$; gate open circuit				
		$dV_{com}/dt = 20\text{ V}/\mu\text{s}$	2.5	-	-	A/ms
		$dV_{com}/dt = 10\text{ V}/\mu\text{s}$	3.5	-	-	A/ms
t_{gt}	gate-controlled turn-on time	$I_{TM} = 20\text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1\text{ A}$; $di_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	μs





$V_o = 1.02 \text{ V}; R_s = 358 \text{ m}\Omega$
 (1) $T_j = 125 \text{ }^\circ\text{C}$; typical values
 (2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values
 (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig 9. On-state current as a function of on-state voltage

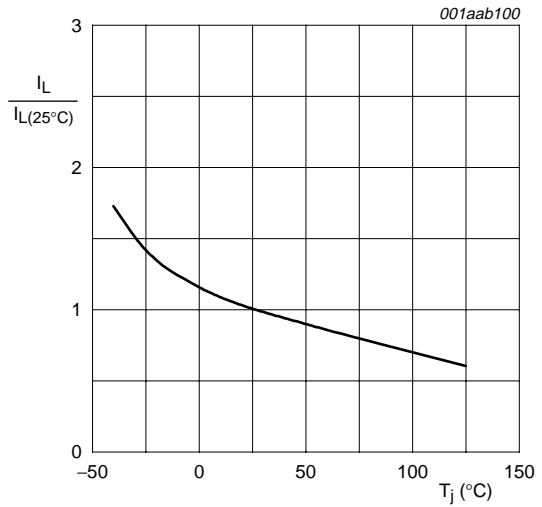


Fig 10. Normalized latching current as a function of junction temperature

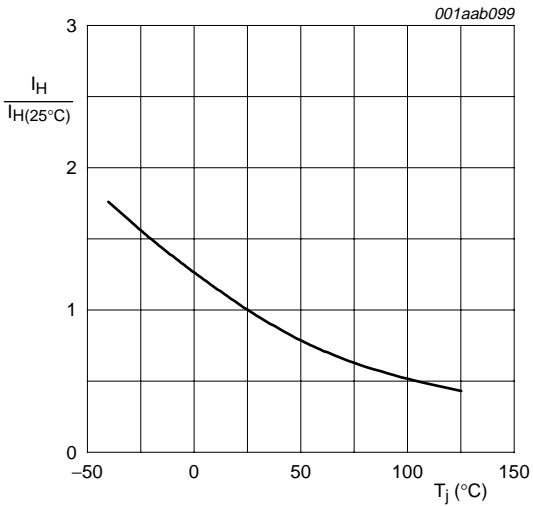
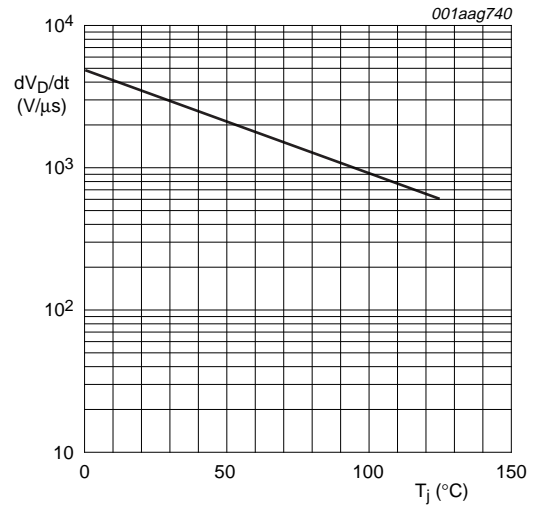


Fig 11. Normalized holding current as a function of junction temperature



Gate open circuit

Fig 12. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

8. Package outline

Plastic surface-mounted package with increased heatsink; 4 leads

SOT223

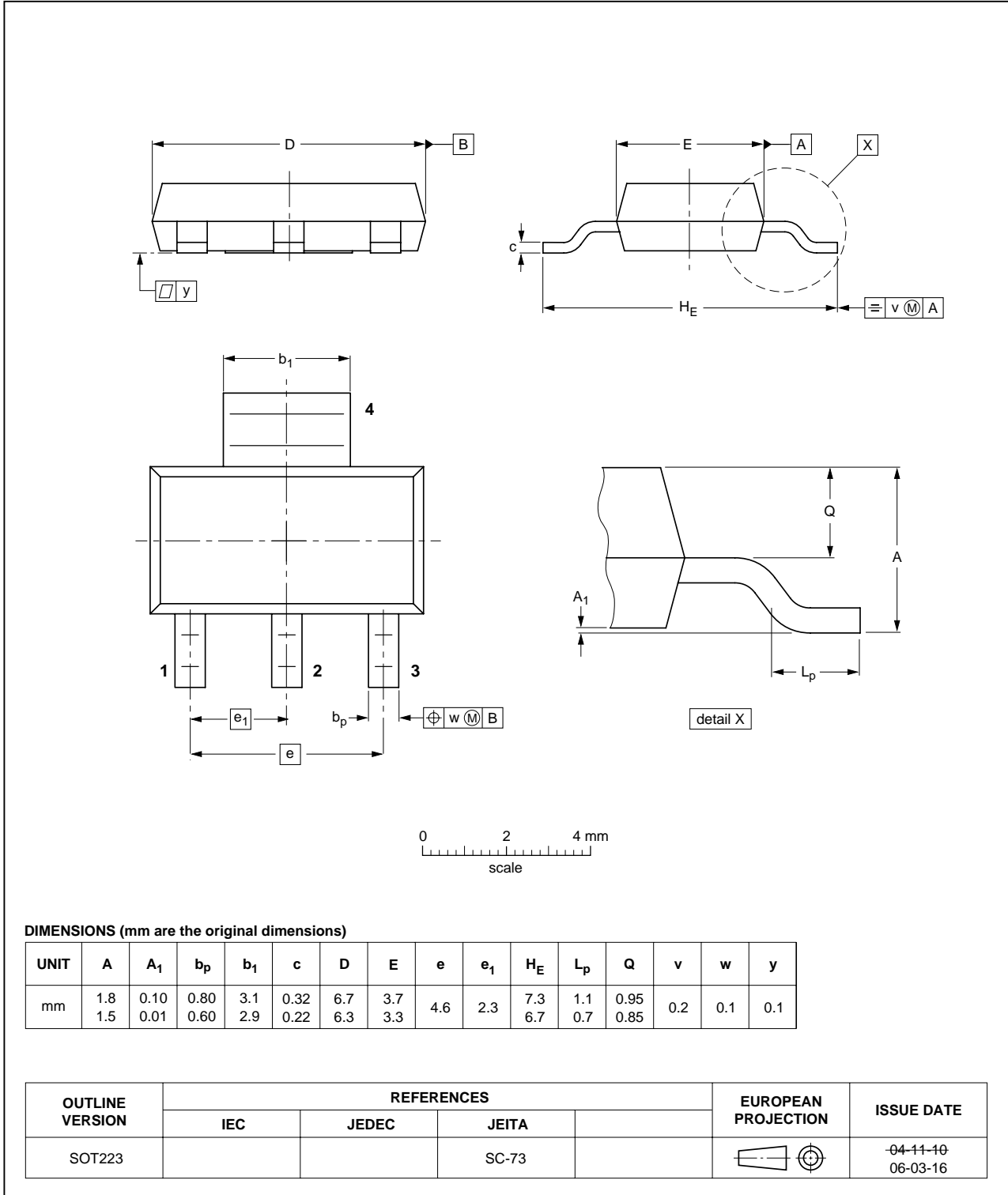
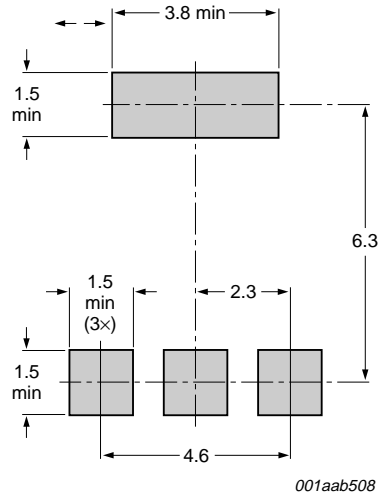


Fig 13. Package outline SOT223

9. Mounting

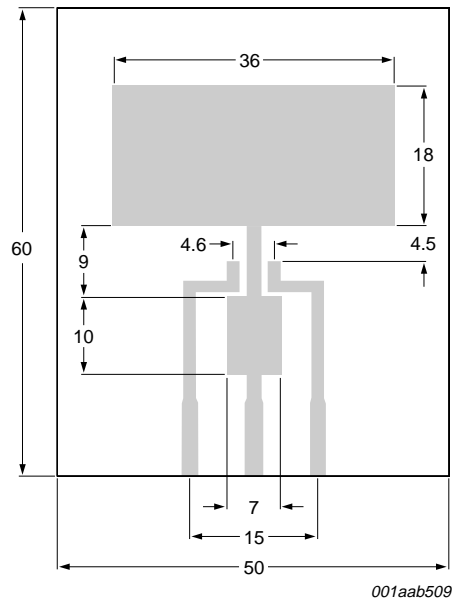
9.1 Mounting instructions



All dimensions are in mm

Fig 14. Minimum footprint SOT223

9.2 Printed-circuit board



All dimensions are in mm

Printed-circuit board: FR4 epoxy glass (1.6 mm thick), copper laminate (35 μm thick)

Fig 15. Printed-circuit board pad area SOT223

10. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA201W_SER_E_3	20080313	Product data sheet	-	BTA201W_SER_E_2
Modifications:		<ul style="list-style-type: none"> • Section 1.4 “Quick reference data” on page 1: Updated with minimum I_{GT} values added. • Table 3 “Limiting values” on page 2: I^2t condition, t_p; symbol update. • Table 5 “Static characteristics” on page 6: Minimum I_G values added. 		
BTA201W_SER_E_2	20070917	Product data sheet	-	BTA201W_SER_E_1
Modifications:		<ul style="list-style-type: none"> • The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Descriptive titles have been corrected. • Table 3 “Limiting values” on page 2: dI_T/dt updated • Table 6 “Dynamic characteristics” on page 7: dV_D/dt updated • Figure “Critical rate of rise of off-state voltage as a function of junction temperature; minimum values” on page 8: graph updated 		
BTA201W_SER_E_1	20060207	Product data sheet	-	-

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Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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